

# NTH4L160N120SC1

Product Preview

## N-Channel Silicon Carbide MOSFET

1200 V, 162 mΩ, 27.3 A

MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	1200	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$	$T_C = 25^\circ\text{C}$	$I_{DC}$	27.3 A
Power Dissipation $R_{\theta JC}$		$P_{DC}$	185 W
Continuous Drain Current $R_{\theta JC}$	$T_C = 100^\circ\text{C}$	$I_{DC}$	19.3 A
Power Dissipation $R_{\theta JC}$		$P_{DC}$	92.5 W
Continuous Drain Current $R_{\theta JA}$	$T_A = 25^\circ\text{C}$	$I_{DA}$	TBD A
Power Dissipation $R_{\theta JA}$		$P_{DA}$	TBD W
Continuous Drain Current $R_{\theta JA}$	$T_A = 100^\circ\text{C}$	$I_{DA}$	TBD A
Power Dissipation $R_{\theta JA}$		$P_{DA}$	TBD W
Pulsed Drain Current $R_{\theta JC}$	$T_C = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$	$I_{DM}$	126 A
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	39.1	A
Single Pulse Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $V_{GS} = 20 \text{ V}$ , $I_{LPK} = 1 \text{ A}$ , $L = 0.1 \text{ mH}$ , $R_G = 25 \Omega$ )	$E_{AS}$	TBD	mJ
Lead Temperature for Soldering Purposes	$T_L$	TBD	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.81	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	TBD	

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

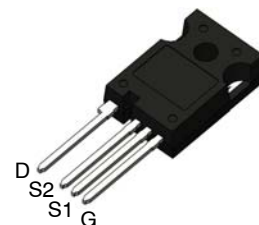
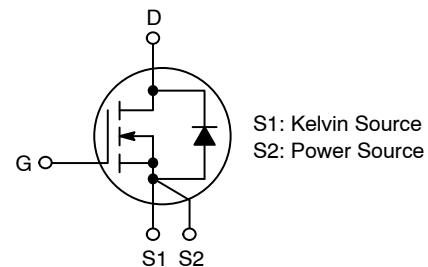


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$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
1200 V	162 mΩ @ 20 V	27.3 A

### N-CHANNEL MOSFET



TO-247-4LD  
CASE 340CJ

### MARKING DIAGRAM



&Z = Assembly Plant Code  
&3 = Data Code (Year & Week)  
&K = Lot  
NTH4L160N120SC1 = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NTH4L160N120SC1

## ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 2.50\text{e} - 04\text{A}, T_C = 25^\circ\text{C}$	1200	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}T_J$	$V_{GS} = 0\text{ V}, I_D = 2.50\text{e} - 04\text{A}, T_{Jmax} = 175^\circ\text{C}$	-	0.25	-	V/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$T_C = 25^\circ\text{C}$	-	-	10.0	$\mu\text{A}$
		$T_C = 175^\circ\text{C}$	-	-	250	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_G = 20\text{ V}, V_D = 0\text{ V}$	-	-	250	nA

### ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_G = 20\text{ V}, I_D = 9.90\text{ A}$	-	162	-	m $\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_G = V_D, I_D = 2.48\text{e} - 03\text{A}$	-	2.83	-	V
Gate Threshold Voltage Temperature Coefficient	$V_{GS(th)}/T_J$		-	-5.37	-	mV/°C
Forward Transconductance	$g_{FS}$	$V_D = 10.0\text{ V}, I_D = 9.90\text{ A}$	-	3.90	-	S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Gate Resistance	$R_G$	$V_G = 0\text{ V}, V_D = 1000\text{ V}$	-	3.09	-	$\Omega$
Input Capacitance	$C_{ISS}$		-	690	-	pF
Reverse Transfer Capacitance	$C_{RSS}$		-	1.92	-	
Output Capacitance	$C_{OSS}$		-	39.1	-	
Effective Output Capacitance	$C_{OSSef}$	$V_{DS} = 0\text{ to }1000\text{ V}, V_G = 0\text{ V}$	-	65.4	-	
Energy Related Output Capacitance	$C_{OSSer}$		-	47.4	-	
Coss Stored Energy	$E_{OSS}$		-	23.7	-	$\mu\text{J}$
Total Gate Charge	$Q_{G(tot)}$	$V_D = 800\text{ V}, I_D = 4.95\text{ A}, V_G = 20\text{ V}$	-	24.1	-	nC
Gate-to-Source Charge	$Q_{GS}$		-	5.95	-	
Gate-to-Drain Charge	$Q_{GD}$		-	5.71	-	

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_G = -5/20\text{ V}, I_D = 9.9\text{ A}, V_D = 800\text{ V}, R_G = 2\ \Omega$	-	-4.37	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	9.74	-	
Rise Time	$t_r$		-	2.81	-	
Fall Time	$t_f$		-	7.65	-	
Turn-On Switching Loss	$E_{ON}$			-	0.06	-
Turn-Off Switching Loss	$E_{OFF}$		-	0.02	-	
Total Switching Loss	$E_{TOT}$		-	0.08	-	

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$I_D = 4.95\text{ A}$	-	3.84	-	V
Reverse Recovery Time	$t_{RR}$	$I_D = 9.9\text{ A}, di/dt = 1000\text{ A}/\mu\text{s}, V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V}$	-	22.3	-	ns
Reverse Recovery Charge	$Q_{RR}$		-	75.6	-	nC
Reverse Recovery Energy	$E_{REC}$		-	19.8	-	$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$		-	5.33	-	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NTH4L160N120SC1

## TYPICAL PERFORMANCE CHARACTERISTICS

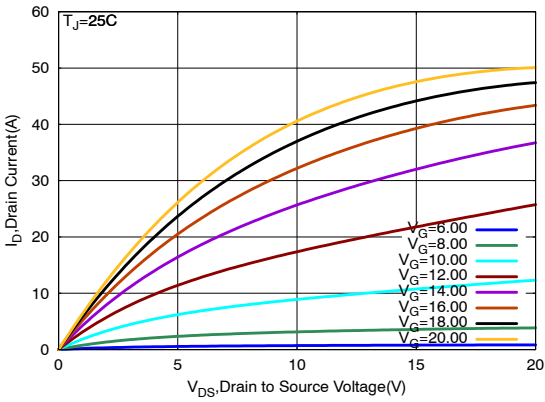


Figure 1. On-Region Characteristics

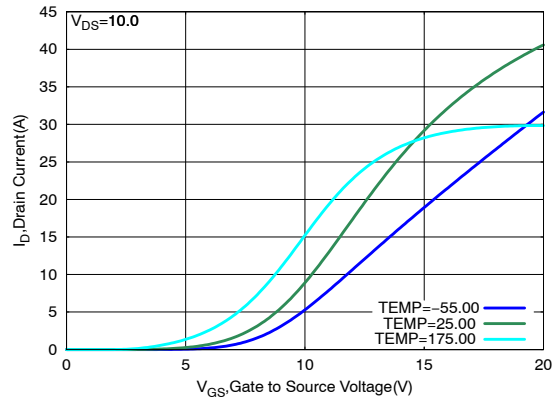


Figure 2. Transfer Characteristics

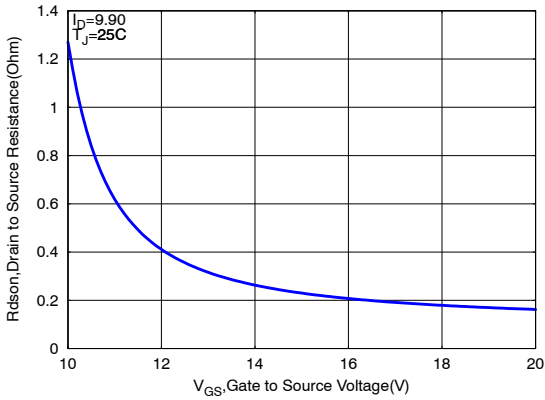


Figure 3. On-Resistance vs. VGS

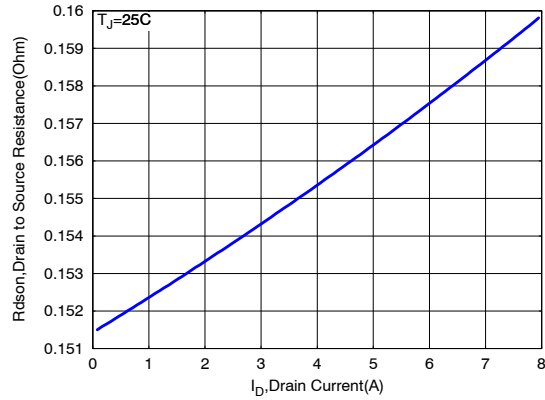


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

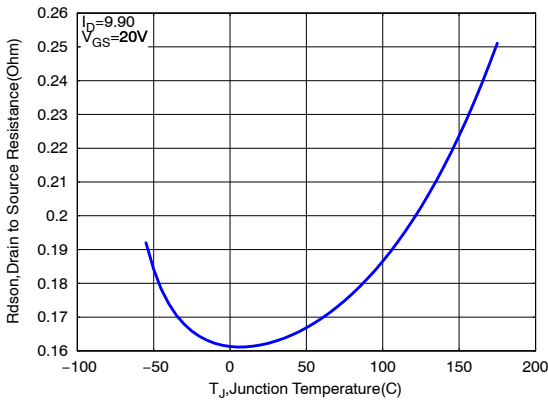


Figure 5. On-Resistance Variation with Temperature

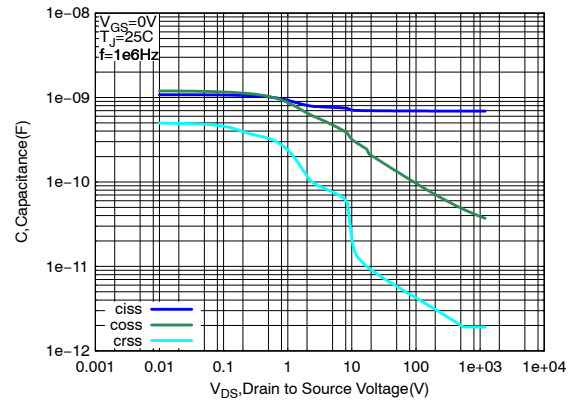


Figure 6. Capacitance Variation

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## TYPICAL PERFORMANCE CHARACTERISTICS

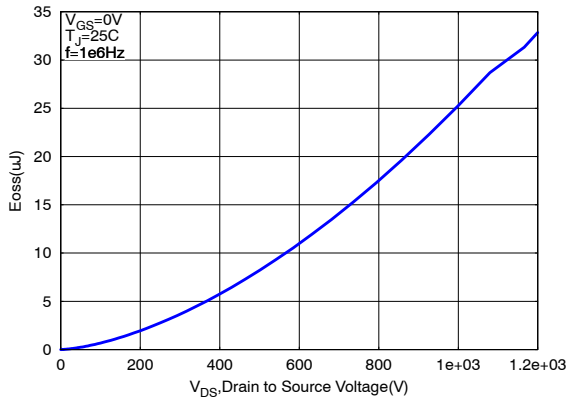


Figure 7. Eoss vs. Drain-to-Source Voltage

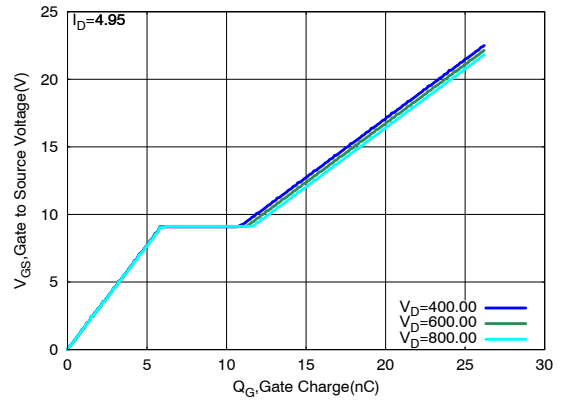


Figure 8. Gate-to-Source Voltage vs. Total Charge

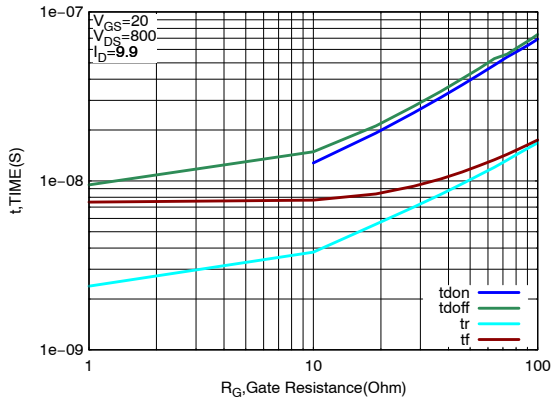


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

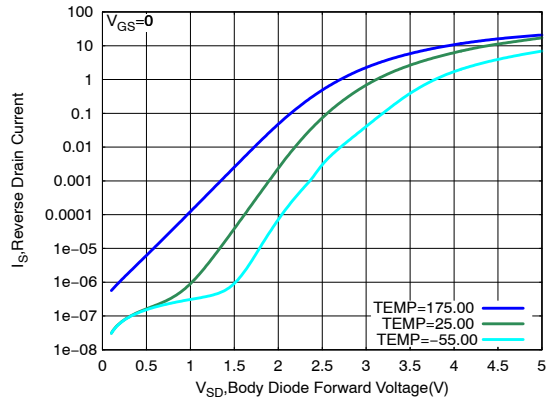


Figure 10. Diode Forward Voltage vs. Current

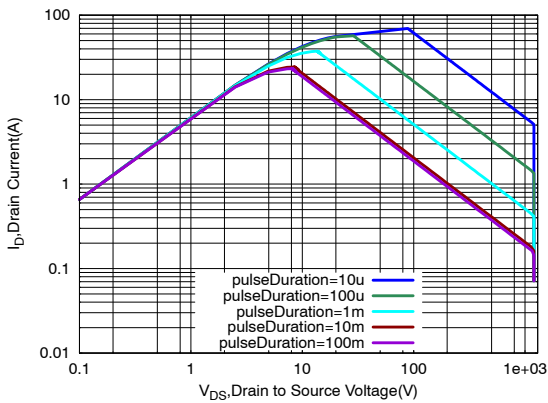


Figure 11. Maximum Rated Forward Biased Safe Operating Area

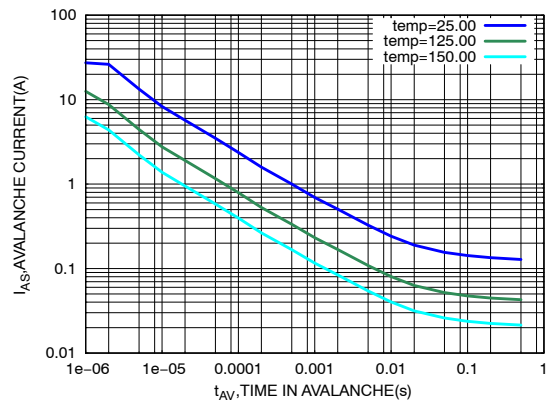


Figure 12. Ipeak vs. Time in Avalanche

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## TYPICAL PERFORMANCE CHARACTERISTICS

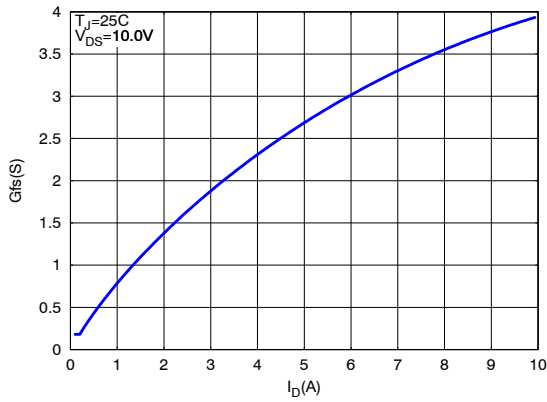


Figure 13. GFS vs. ID

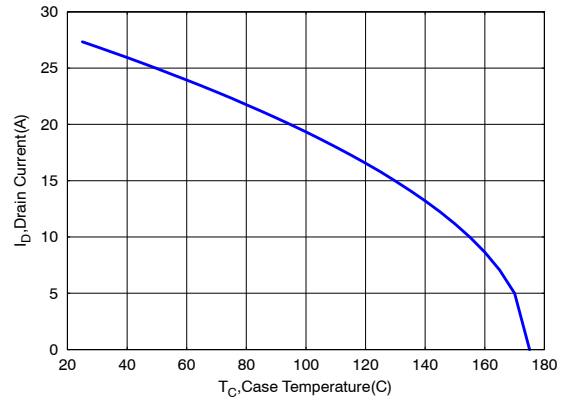


Figure 14. Maximum Current vs. Case Temperature

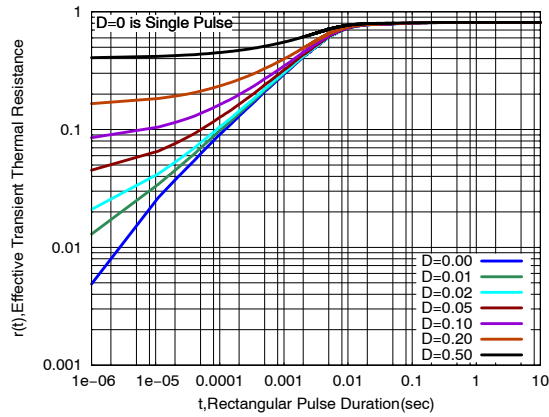


Figure 15. Thermal Response

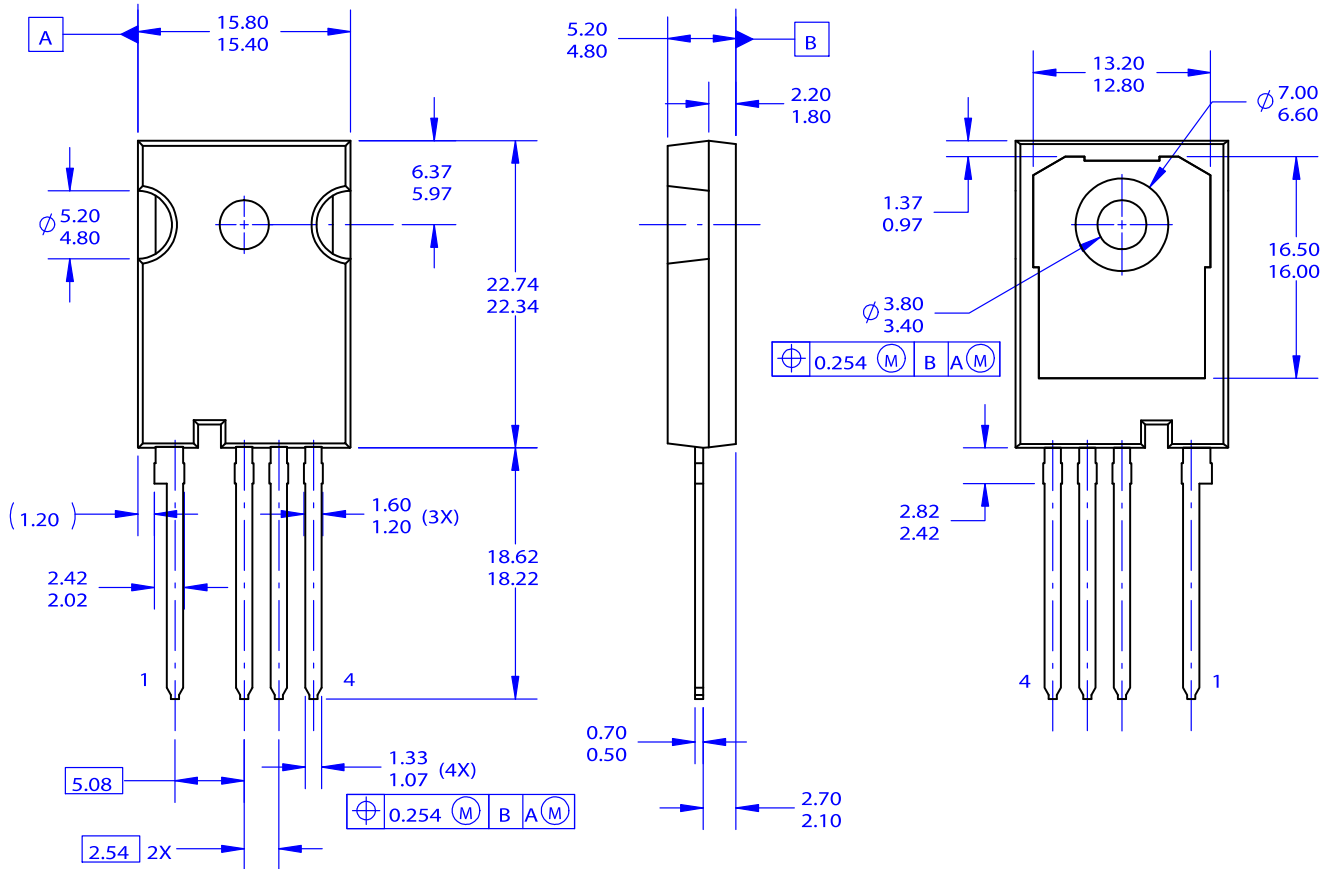
### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTH4L160N120SC1	NTH4L160N120SC1	TO-247	Tube	N/A	N/A	30 Units

# NTH4L160N120SC1

## PACKAGE DIMENSIONS

TO-247-4LD  
CASE 340CJ  
ISSUE O



### NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

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